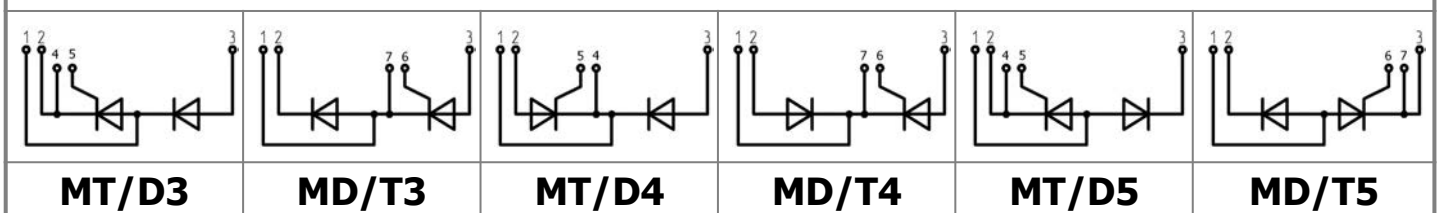
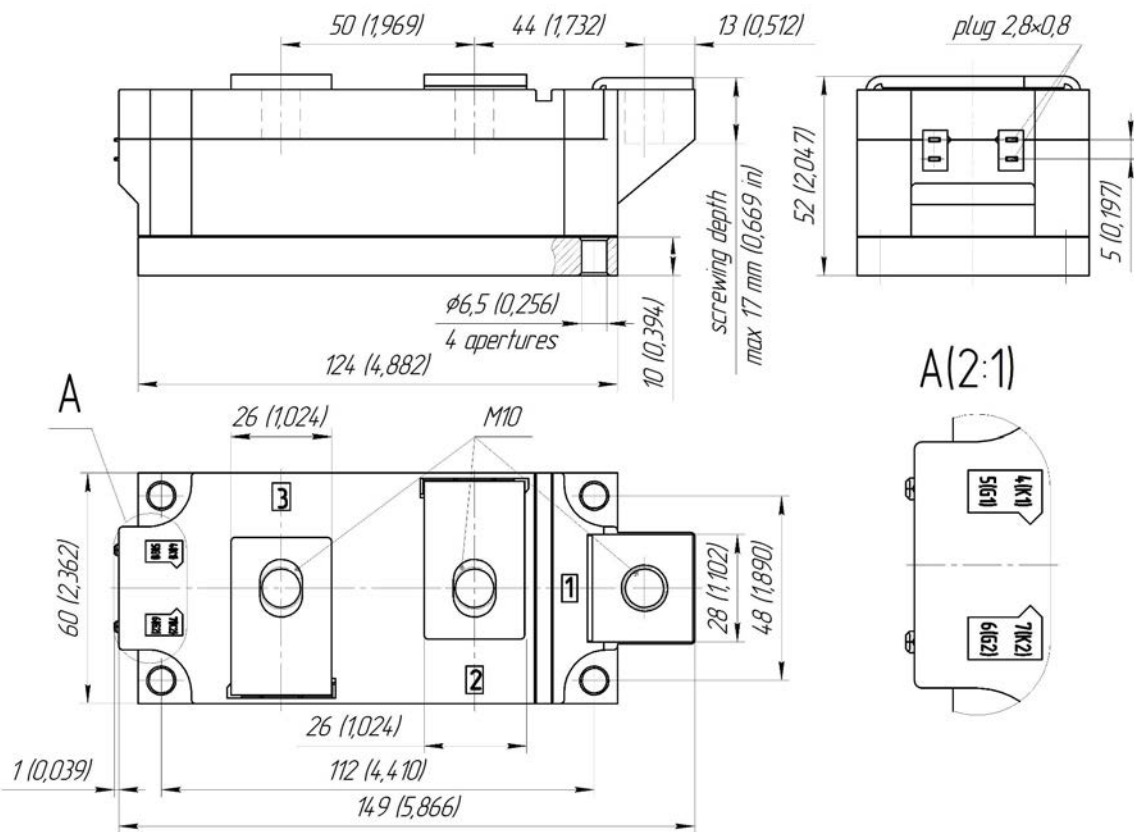
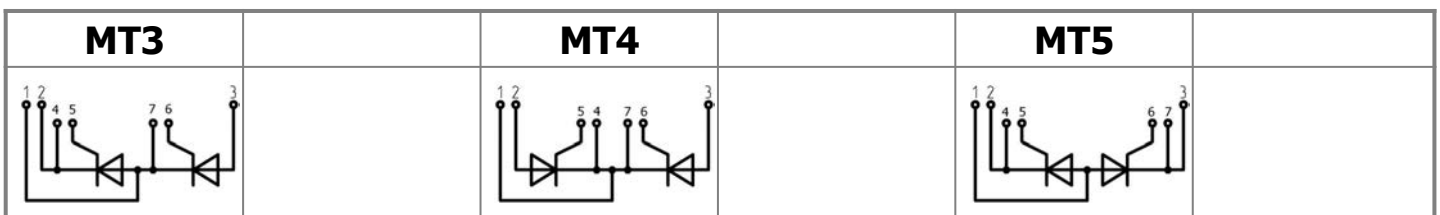




Thyristor Modules MTx-260-44-A2



Mean on-state current			I_{TAV}	260 A
Repetitive peak off-state voltage			V_{DRM}	3800...4400 V
Repetitive peak reverse voltage			V_{RRM}	
Turn-off time			t_q	500 μ s
V_{DRM}, V_{RRM}, V	3800	4000	4200	4400
Voltage code	38	40	42	44
$T_j, ^\circ C$	-40...+125			



MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions
ON-STATE				
I_{TAV}	Maximum allowable mean on-state current	A	260 334	$T_c = 96\text{ }^\circ\text{C}$; $T_c = 85\text{ }^\circ\text{C}$; 180° half-sine wave; 50 Hz
I_{TRMS}	RMS on-state current	A	408	$T_c = 96\text{ }^\circ\text{C}$; 180° half-sine wave; 50 Hz
I_{TSM}	Surge on-state current	kA	6.5 7.5	$T_j = T_{j\max}$ $T_j = 25\text{ }^\circ\text{C}$ 180° half-sine wave; $t_p = 10\text{ ms}$; single pulse; $V_D = V_R = 0\text{ V}$; Gate pulse: $I_G = 2\text{ A}$; $t_{GP} = 50\text{ }\mu\text{s}$; $di_G/dt \geq 1\text{ A}/\mu\text{s}$
			7.0 8.0	$T_j = T_{j\max}$ $T_j = 25\text{ }^\circ\text{C}$ 180° half-sine wave; $t_p = 8.3\text{ ms}$; single pulse; $V_D = V_R = 0\text{ V}$; Gate pulse: $I_G = 2\text{ A}$; $t_{GP} = 50\text{ }\mu\text{s}$; $di_G/dt \geq 1\text{ A}/\mu\text{s}$
I^2t	Safety factor	$A^2s \cdot 10^3$	210 280	$T_j = T_{j\max}$ $T_j = 25\text{ }^\circ\text{C}$ 180° half-sine wave; $t_p = 10\text{ ms}$; single pulse; $V_D = V_R = 0\text{ V}$; Gate pulse: $I_G = 2\text{ A}$; $t_{GP} = 50\text{ }\mu\text{s}$; $di_G/dt \geq 1\text{ A}/\mu\text{s}$
			200 260	$T_j = T_{j\max}$ $T_j = 25\text{ }^\circ\text{C}$ 180° half-sine wave; $t_p = 8.3\text{ ms}$; single pulse; $V_D = V_R = 0\text{ V}$; Gate pulse: $I_G = 2\text{ A}$; $t_{GP} = 50\text{ }\mu\text{s}$; $di_G/dt \geq 1\text{ A}/\mu\text{s}$
BLOCKING				
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	3800...4400	$T_{j\min} < T_j < T_{j\max}$; 180° half-sine wave; 50 Hz; Gate open
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	3900...4500	$T_{j\min} < T_j < T_{j\max}$; 180° half-sine wave; single pulse; Gate open
V_{D}, V_R	Direct off-state and Direct reverse voltages	V	$0.6 \cdot V_{DRM}$ $0.6 \cdot V_{RRM}$	$T_j = T_{j\max}$; Gate open
TRIGGERING				
I_{FGM}	Peak forward gate current	A	8	$T_j = T_{j\max}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	4	$T_j = T_{j\max}$ for DC gate current
SWITCHING				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive ($f = 1\text{ Hz}$)	$A/\mu\text{s}$	500	$T_j = T_{j\max}$; $V_D = 0.67 \cdot V_{DRM}$; $I_{TM} = 1250\text{ A}$; Gate pulse: $I_G = 2\text{ A}$; $t_{GP} = 50\text{ }\mu\text{s}$; $di_G/dt \geq 2\text{ A}/\mu\text{s}$
THERMAL				
T_{stg}	Storage temperature	$^\circ\text{C}$	-40...+50	
T_j	Operating junction temperature	$^\circ\text{C}$	-40...+125	
$T_{c\text{ op}}$	Operating temperature	$^\circ\text{C}$	-40...+125	
MECHANICAL				
a	Acceleration under vibration	m/s^2	50	

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{TM}	Peak on-state voltage, max	V	2.00	$T_j=25\text{ }^\circ\text{C}; I_{TM}=628\text{ A}$	
$V_{T(TO)}$	On-state threshold voltage, max	V	1.267	$T_j=T_{j\text{ max}};$	
r_T	On-state slope resistance, max	m Ω	1.112	$0.5\pi I_{TAV} < I_T < 1.5\pi I_{TAV}$	
I_L	Latching current, max	mA	1000	$T_j=25\text{ }^\circ\text{C}; V_D=12\text{ V};$ Gate pulse: $I_G=2\text{ A};$ $t_{GP}=50\text{ }\mu\text{s}; di_G/dt\geq 1\text{ A}/\mu\text{s}$	
I_H	Holding current, max	mA	300	$T_j=25\text{ }^\circ\text{C};$ $V_D=12\text{ V};$ Gate open	
BLOCKING					
I_{DRM}, I_{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	100 3.00	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^\circ\text{C}$	$V_D=V_{DRM}; V_R=V_{RRM}$
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage ¹⁾ , min	V/ μs	200, 320, 500, 1000, 1600, 2000, 2500	$T_j=T_{j\text{ max}};$ $V_D=0.67\cdot V_{DRM};$ Gate open	
TRIGGERING					
V_{GT}	Gate trigger direct voltage, max	V	3.00 2.50 1.50	$T_j=T_{j\text{ min}}$ $T_j=25\text{ }^\circ\text{C}$ $T_j=T_{j\text{ max}}$	$V_D=12\text{ V}; I_D=3\text{ A};$ Direct gate current
I_{GT}	Gate trigger direct current, max	mA	400 250 150	$T_j=T_{j\text{ min}}$ $T_j=25\text{ }^\circ\text{C}$ $T_j=T_{j\text{ max}}$	
V_{GD}	Gate non-trigger direct voltage, min	V	0.45	$T_j=T_{j\text{ max}};$ $V_D=0.67\cdot V_{DRM};$	
I_{GD}	Gate non-trigger direct current, min	mA	55.00	Direct gate current	
SWITCHING					
t_{gd}	Delay time, max	μs	3.20	$T_j=25\text{ }^\circ\text{C}; V_D=1500\text{ V}; I_{TM}=I_{TAV};$ $di/dt=200\text{ A}/\mu\text{s};$	
t_{gt}	Turn-on time, max	μs	15.0	Gate pulse: $I_G=2\text{ A}; V_G=20\text{ V};$ $t_{GP}=50\text{ }\mu\text{s}; di_G/dt=2\text{ A}/\mu\text{s}$	
t_q	Turn-off time ²⁾ , max	μs	500	$dv_D/dt=50\text{ V}/\mu\text{s}; T_j=T_{j\text{ max}}; I_{TM}=I_{TAV};$ $di_R/dt=10\text{ A}/\mu\text{s}; V_R=100\text{ V};$ $V_D=0.67\text{ }V_{DRM};$	
Q_{rr}	Recovered charge, max	μC	1580	$T_j=T_{j\text{ max}}; I_{TM}=I_{TAV};$	
t_{rr}	Reverse recovery time, max	μs	40	$di_R/dt=-5\text{ A}/\mu\text{s};$	
I_{rr}	Reverse recovery current, max	A	79	$V_R=100\text{ V};$	
THERMAL					
R_{thjc}	Thermal resistance, junction to case				
	per module	$^\circ\text{C}/\text{W}$	0.0275	180° half-sine wave, 50 Hz	
	per arm	$^\circ\text{C}/\text{W}$	0.0550		
	per module	$^\circ\text{C}/\text{W}$	0.0265	DC	
per arm	$^\circ\text{C}/\text{W}$	0.0530			
R_{thch}	Thermal resistance, case to heatsink				
	per module	$^\circ\text{C}/\text{W}$	0.0100		
	per arm	$^\circ\text{C}/\text{W}$	0.0200		
INSULATION					
V_{ISOL}	Insulation test voltage	kV	3.00	Sine wave, 50 Hz;	t=60 sec
			3.60	RMS	t=1 sec
MECHANICAL					
M_1	Mounting torque (M6) ³⁾	Nm	6.00	Tolerance $\pm 15\%$	
M_2	Terminal connection torque (M10) ³⁾	Nm	12.00	Tolerance $\pm 15\%$	
m	Weight, max	g	1500		

PART NUMBERING GUIDE									NOTES																											
MT	3	-	260	-	44	-	A2	E2	-	A2	-	N	1) Critical rate of rise of off-state voltage <table border="1"> <thead> <tr> <th>Symbol of Group</th> <th>P2</th> <th>K2</th> <th>E2</th> <th>A2</th> <th>T1</th> <th>P1</th> <th>M1</th> </tr> </thead> <tbody> <tr> <td>$(dv_D/dt)_{crit}, V/\mu s$</td> <td>200</td> <td>320</td> <td>500</td> <td>1000</td> <td>1600</td> <td>2000</td> <td>2500</td> </tr> </tbody> </table>								Symbol of Group	P2	K2	E2	A2	T1	P1	M1	$(dv_D/dt)_{crit}, V/\mu s$	200	320	500	1000	1600	2000	2500
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1	2	3	4	5	6	7	8																													
1. Thyristor module (MT) Thyristor – Diode module (MT/D) Diode – Thyristor module (MD/T) 2. Circuit Schematic: 3 – serial connection 4 – common Cathode 5 – common Anode 3. Average On-state Current, A 4. Voltage Code 5. Critical rate of rise of off-state voltage 6. Group of turn-off time ($dv_D/dt=50 V/\mu s$) 7. Package Type (M.A2) 8. Ambient Conditions: N – Normal									2) Turn-off time ($dv_D/dt=50 V/\mu s$) <table border="1"> <thead> <tr> <th>Symbol of Group</th> <th>E2</th> </tr> </thead> <tbody> <tr> <td>$t_{q}, \mu s$</td> <td>500</td> </tr> </tbody> </table>								Symbol of Group	E2	$t_{q}, \mu s$	500																
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									3) The screws must be lubricated																											

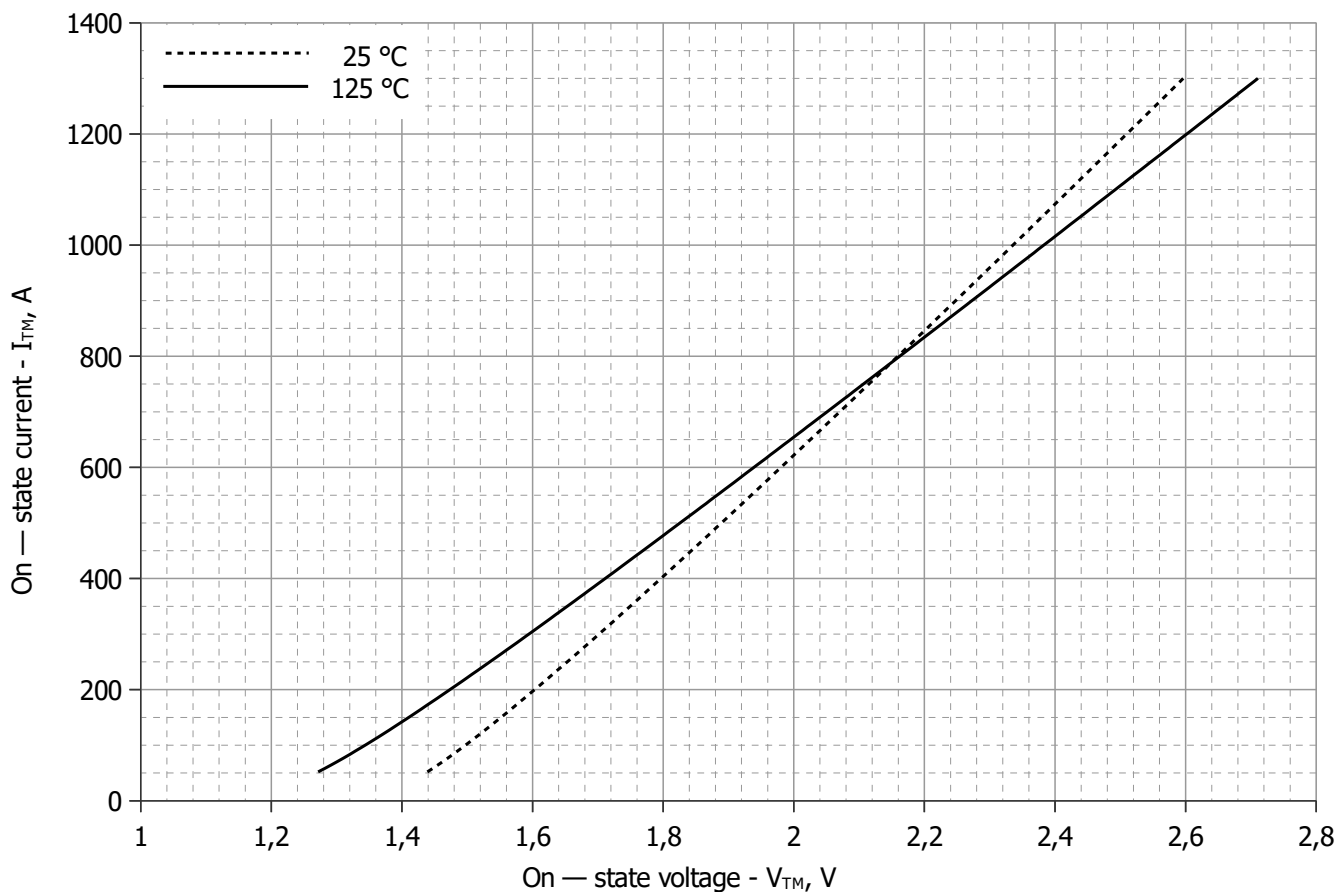


Fig 1 – On-state characteristics of Limit device

Analytical function for On-state characteristic:

$$V_T = A + B \cdot i_T + C \cdot \ln(i_T + 1) + D \cdot \sqrt{i_T}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j,\text{max}}$
A	1.32253416	1.10489155
B	0.00078733	0.00103823
C	0.01003232	0.02426251
D	0.00494719	0.00227858

On-state characteristic model (see Fig. 1)

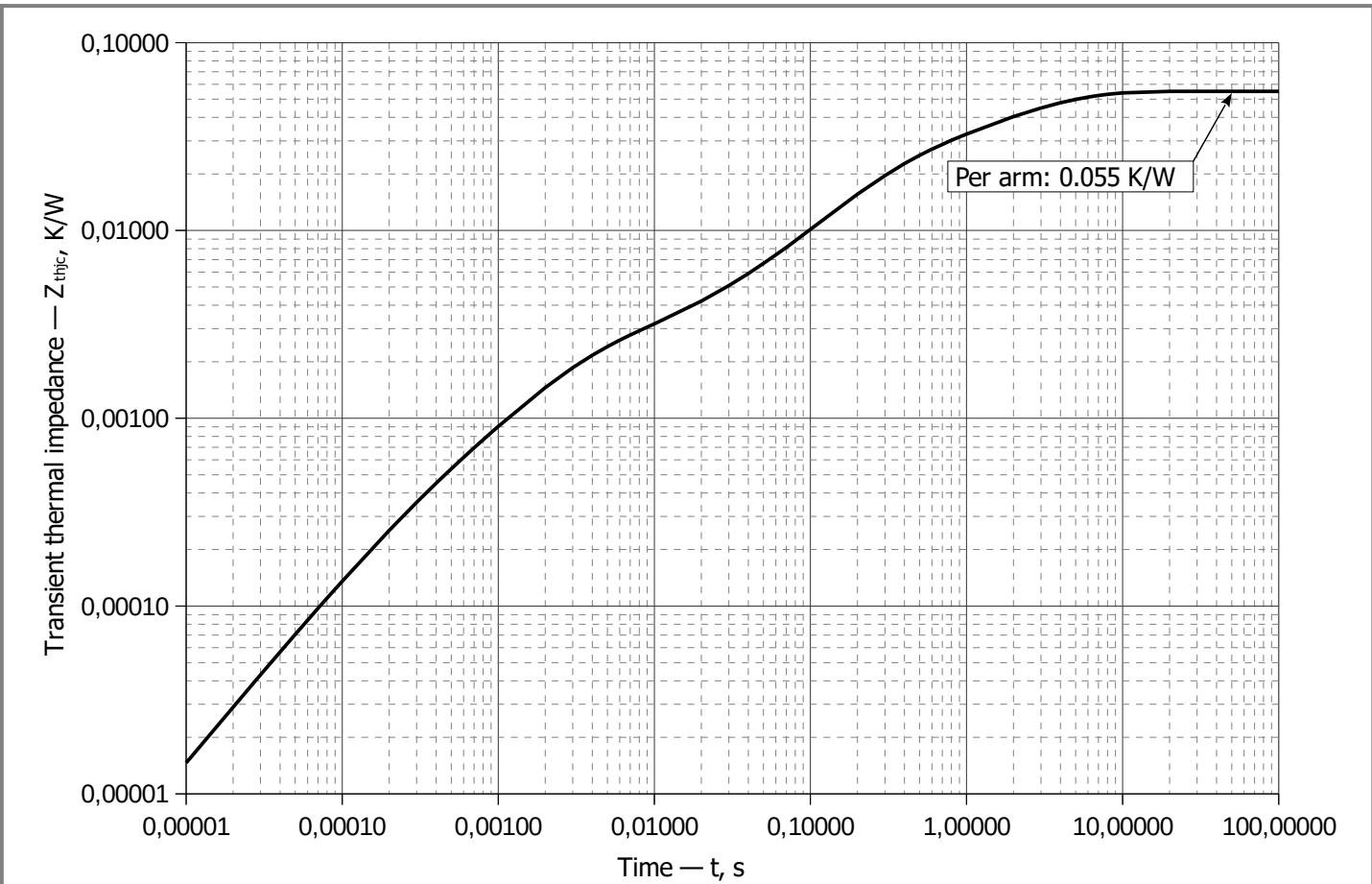


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

i	1	2	3	4	5	6
R_i, K/W	0.0249	0.0112	0.01635	0.0006528	0.001791	0.0001363
τ_i, s	3.132	1.000	0.2335	0.01038	0.002348	0.0002448

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

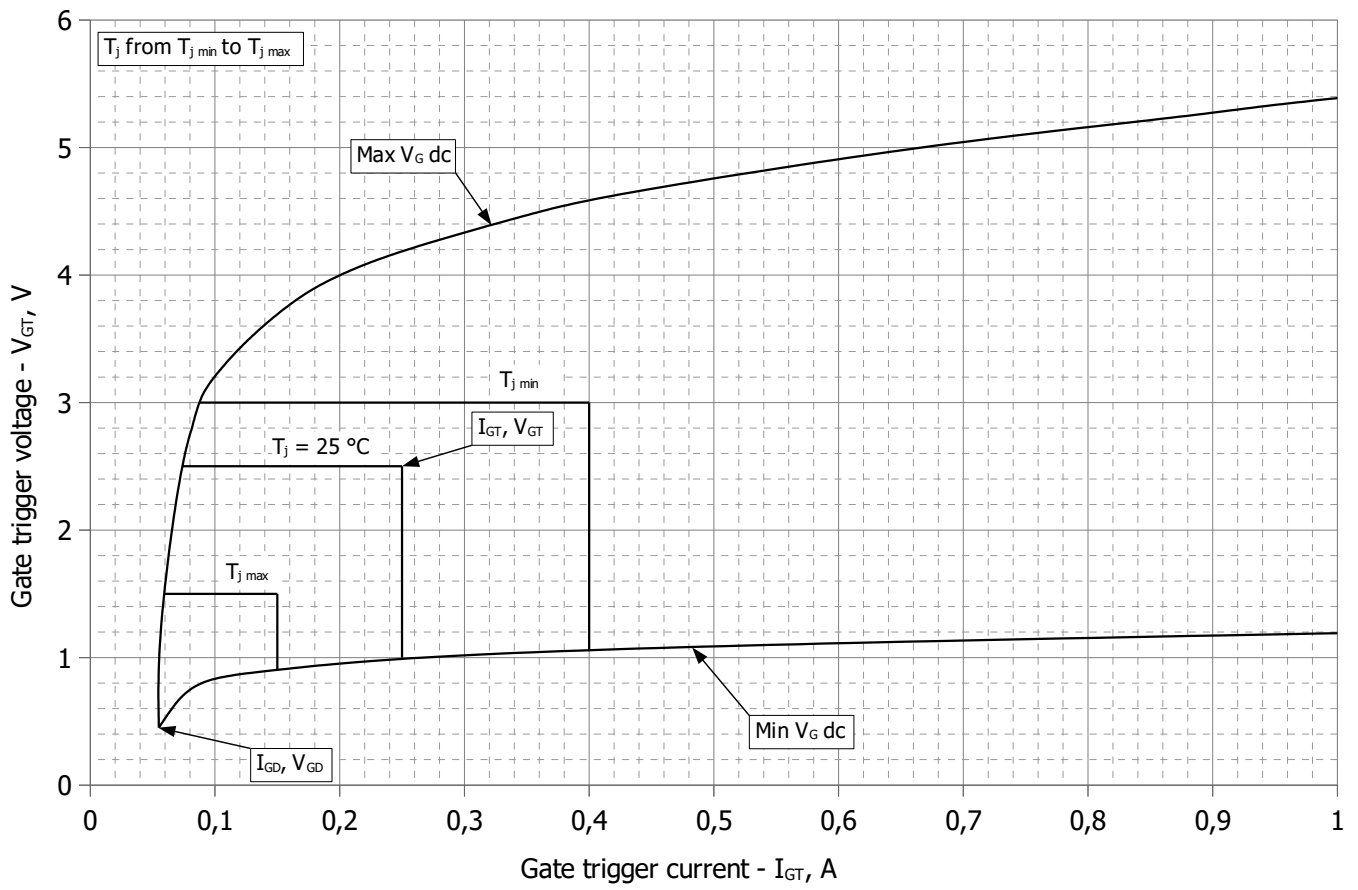


Fig 3 – Gate characteristics – Trigger limits

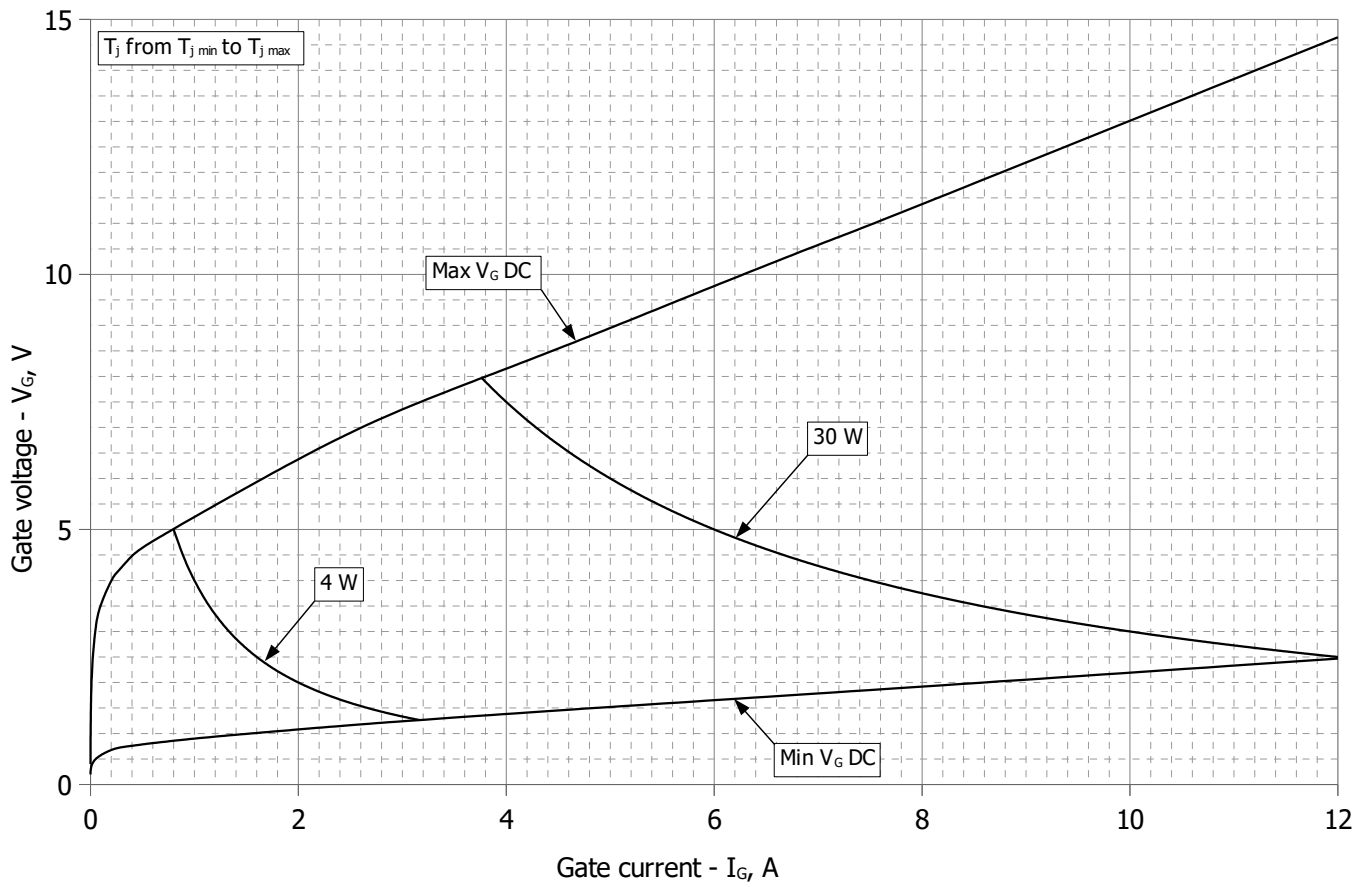


Fig 4 - Gate characteristics – Power curves

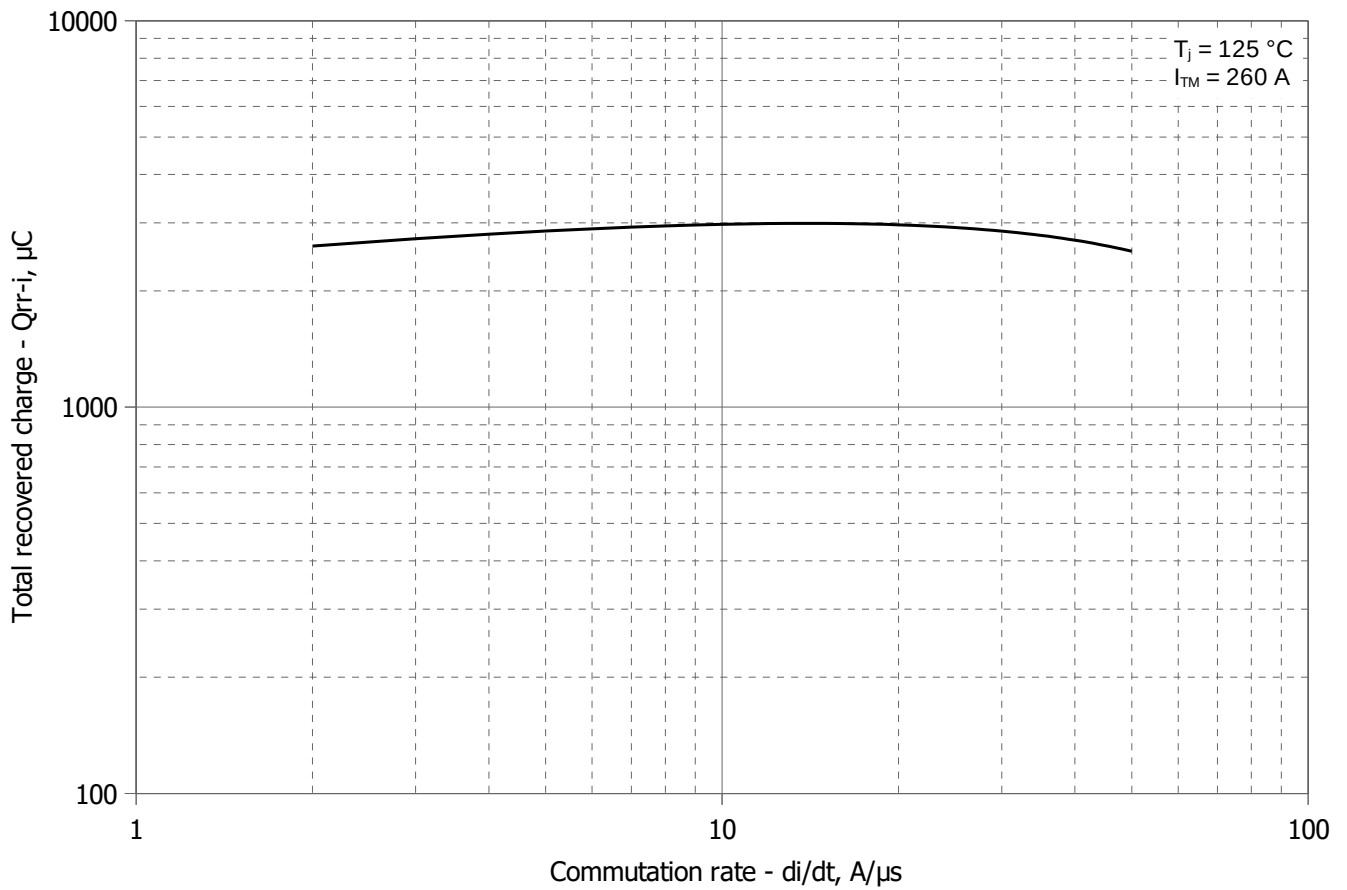


Fig 5 – Maximum recovered charge Q_{rr-i} (integral) vs. commutation rate di_R/dt

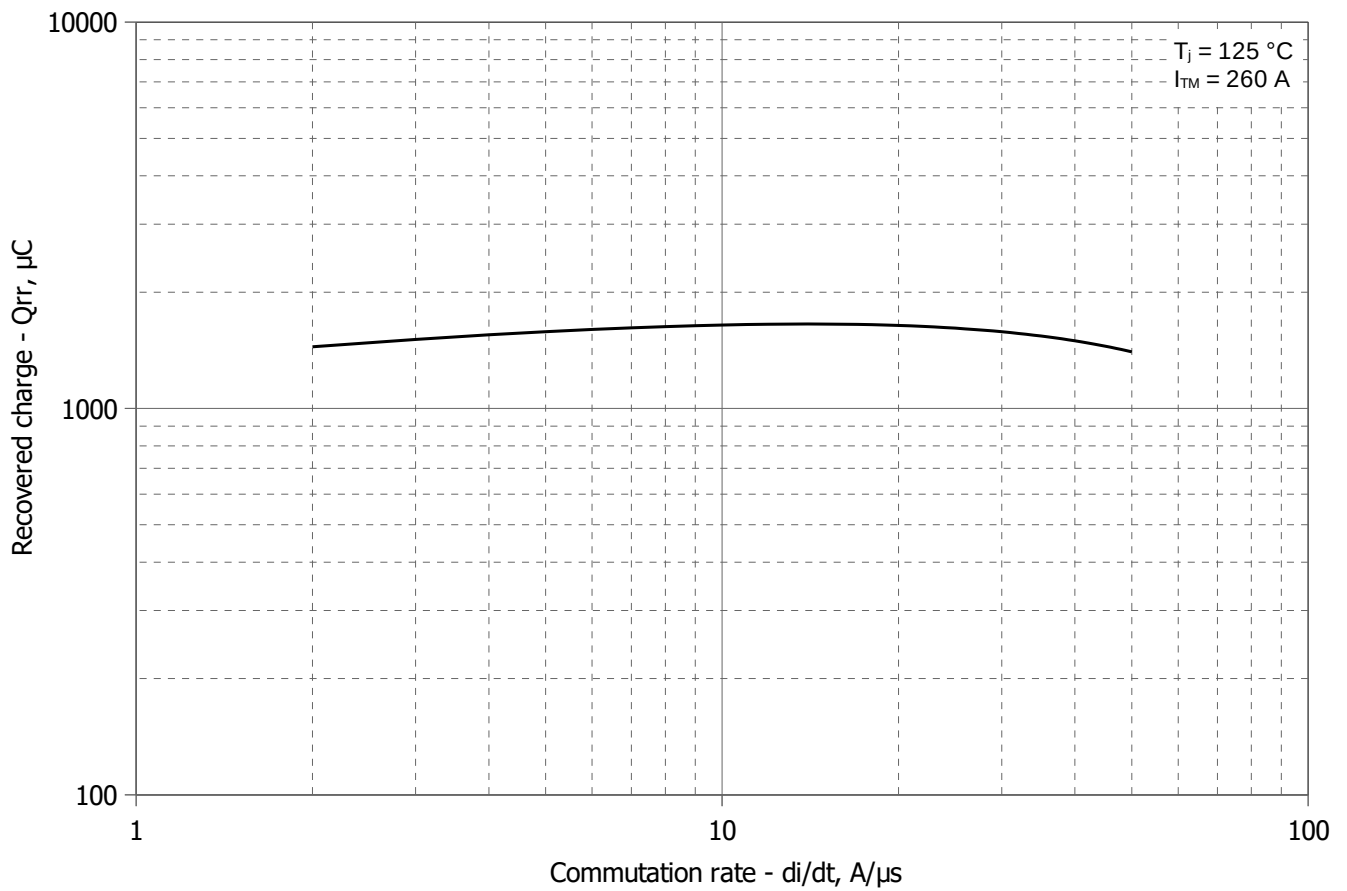


Fig 6 – Maximum recovered charge Q_{rr} vs. commutation rate di_R/dt (25% chord)

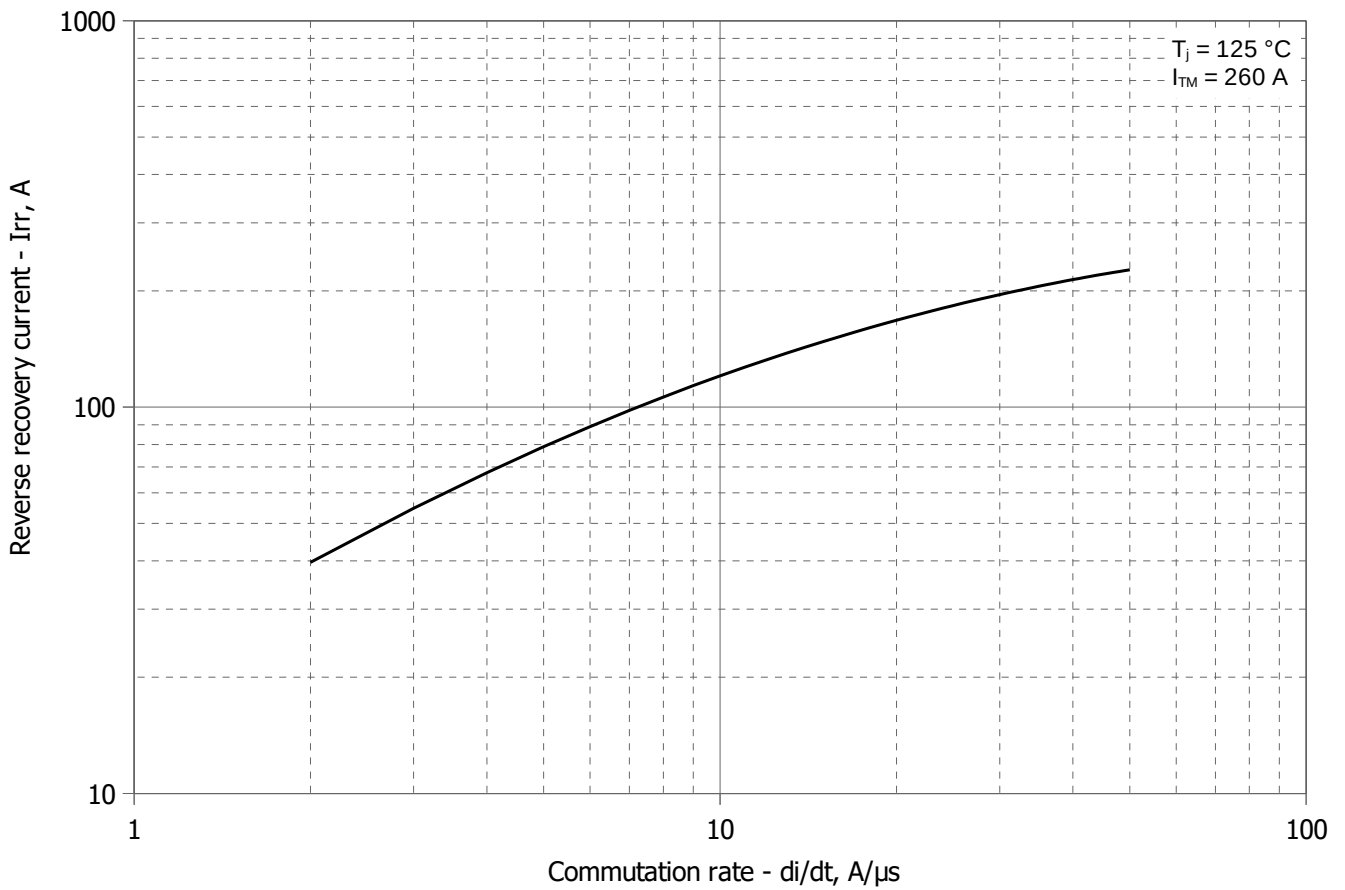


Fig 7 – Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

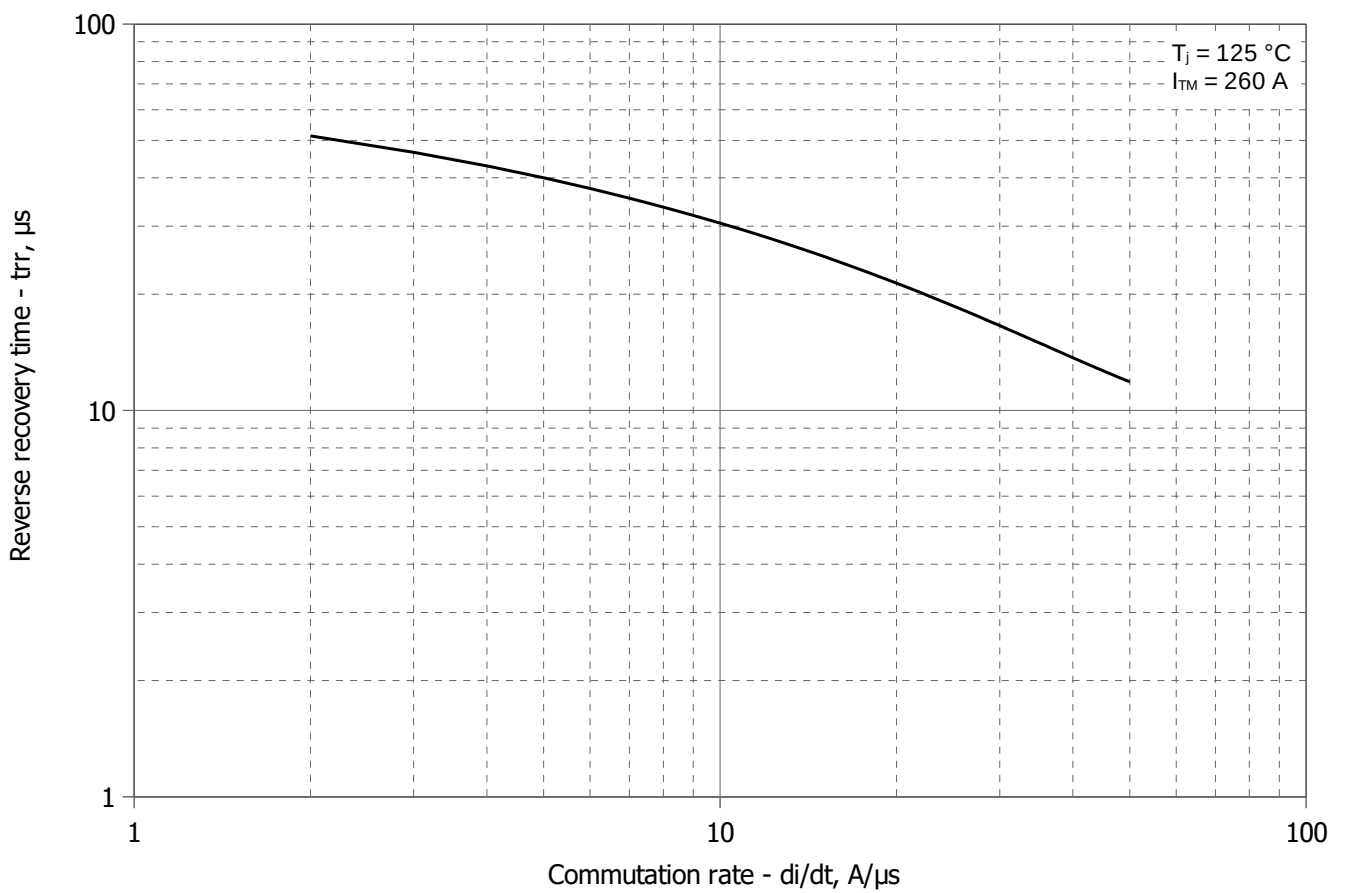


Fig 8 – Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)

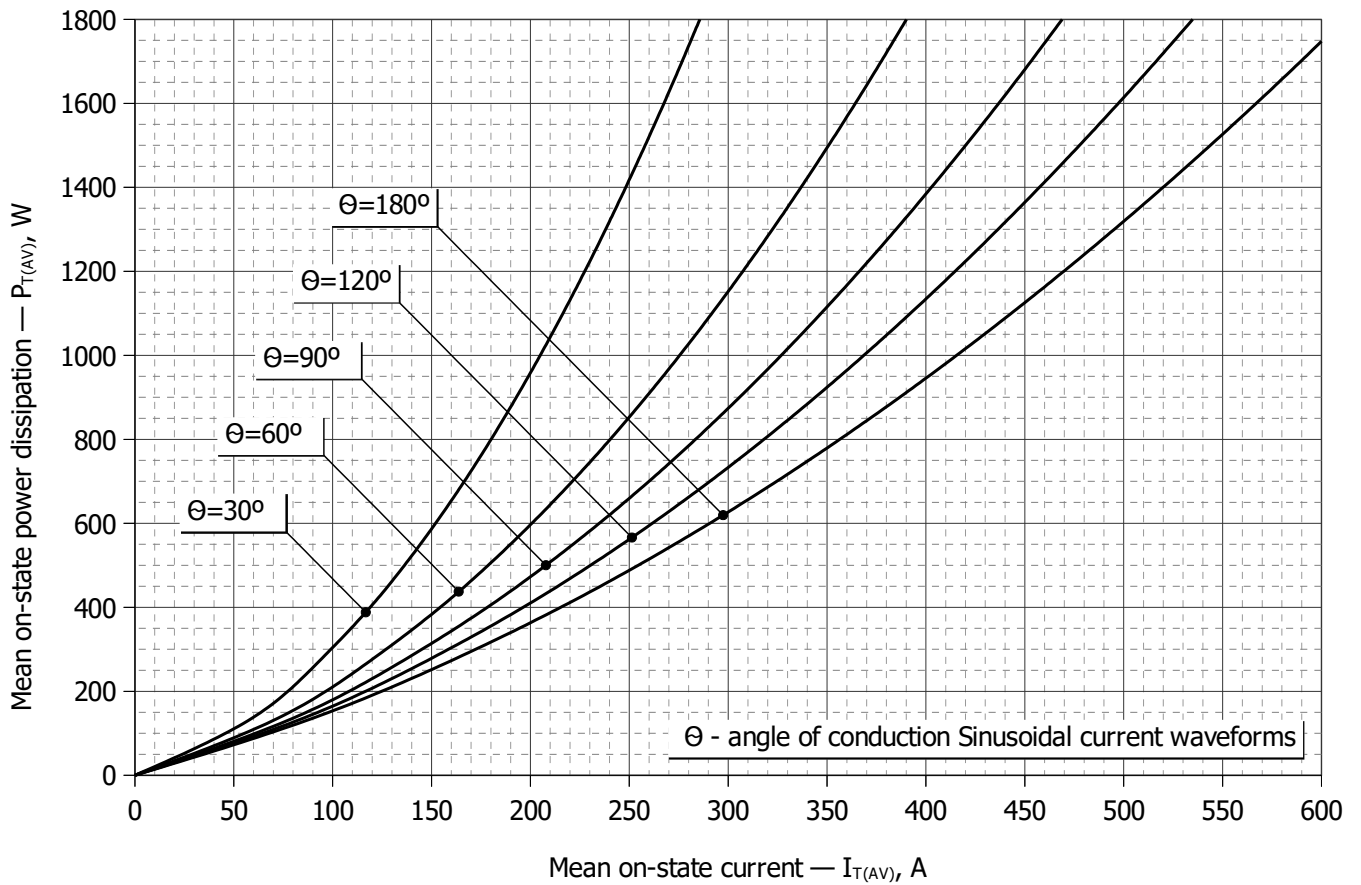


Fig. 9 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$)

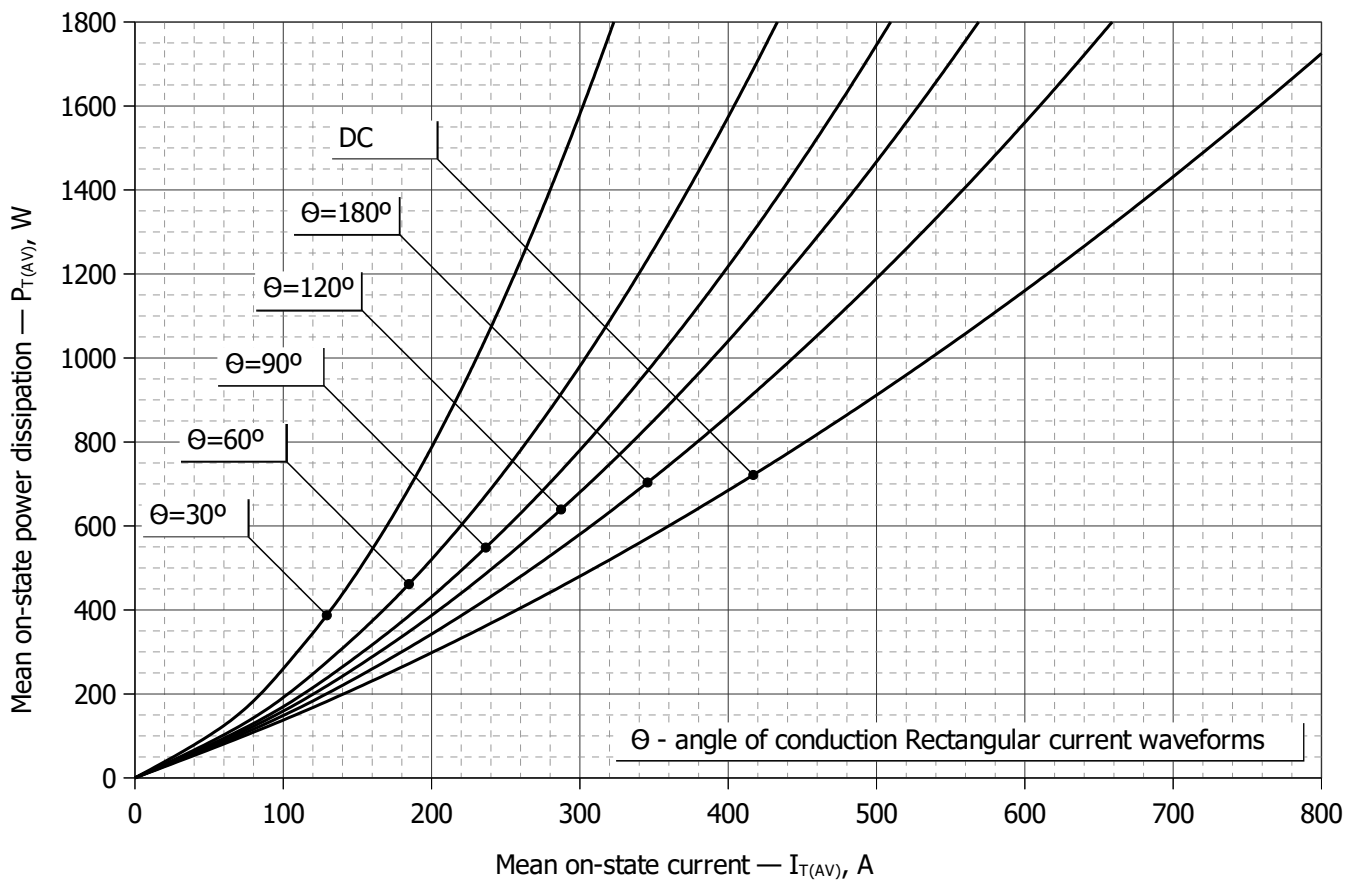


Fig. 10 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$)

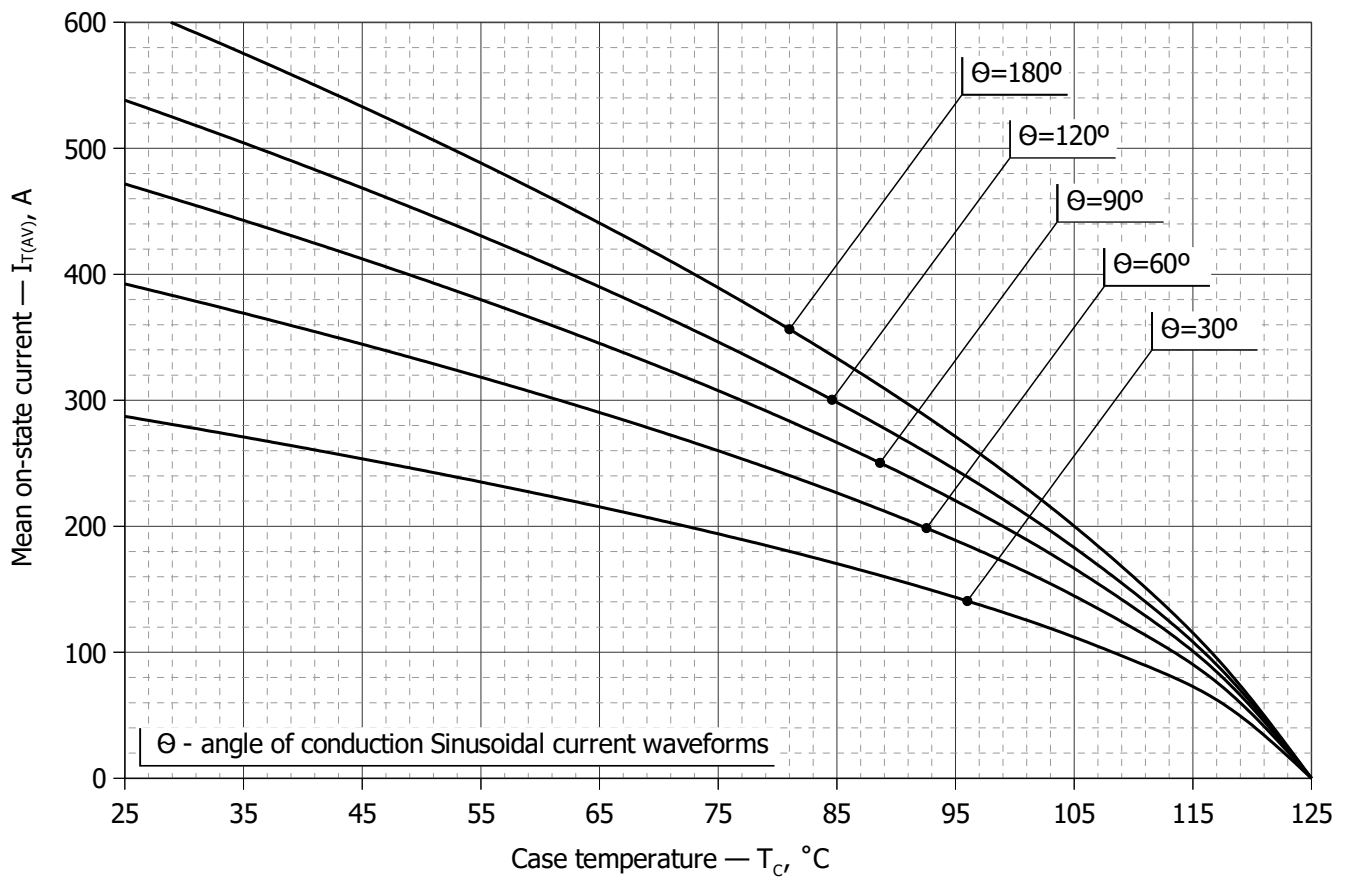


Fig. 11 – Mean on-state current I_{TAV} vs. case temperature T_c for sinusoidal current waveforms at different conduction angles ($f=50Hz$)

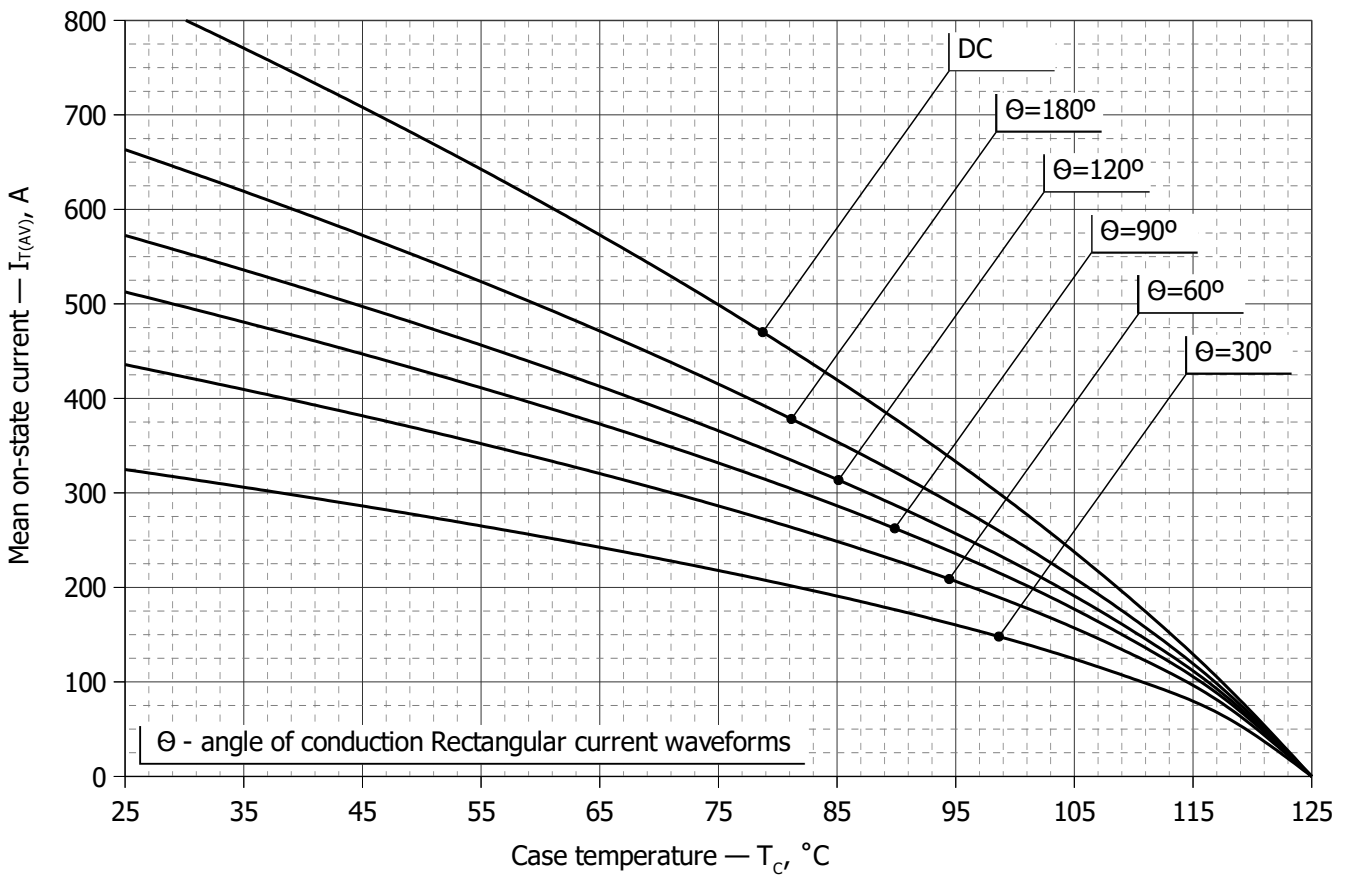


Fig. 12 - Mean on-state current I_{TAV} vs. case temperature T_c for rectangular current waveforms at different conduction angles and for DC ($f=50Hz$)

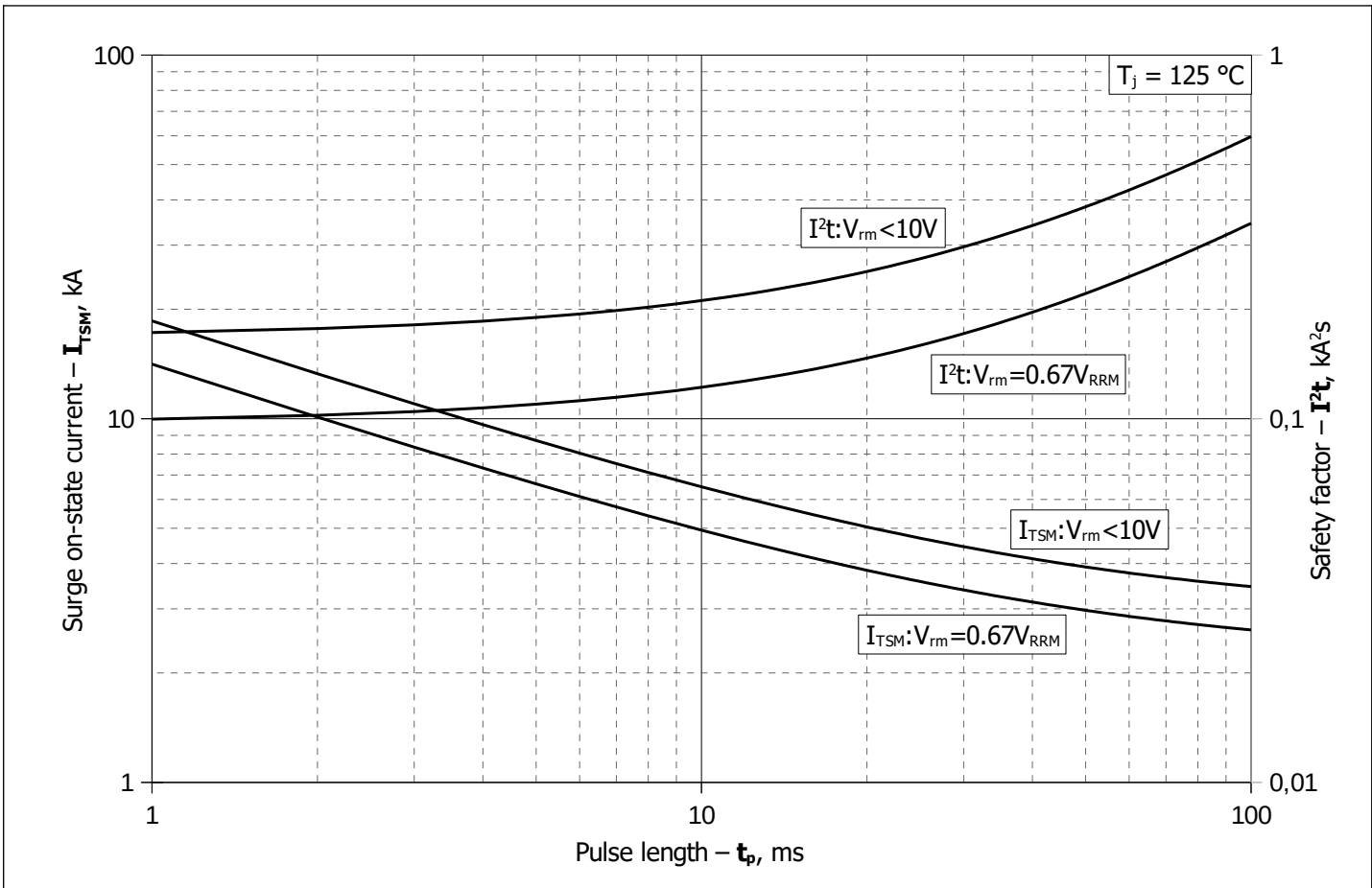


Fig. 13 – Maximum surge on-state current I_{TSM} and safety factor I^2t vs. pulse length t_p

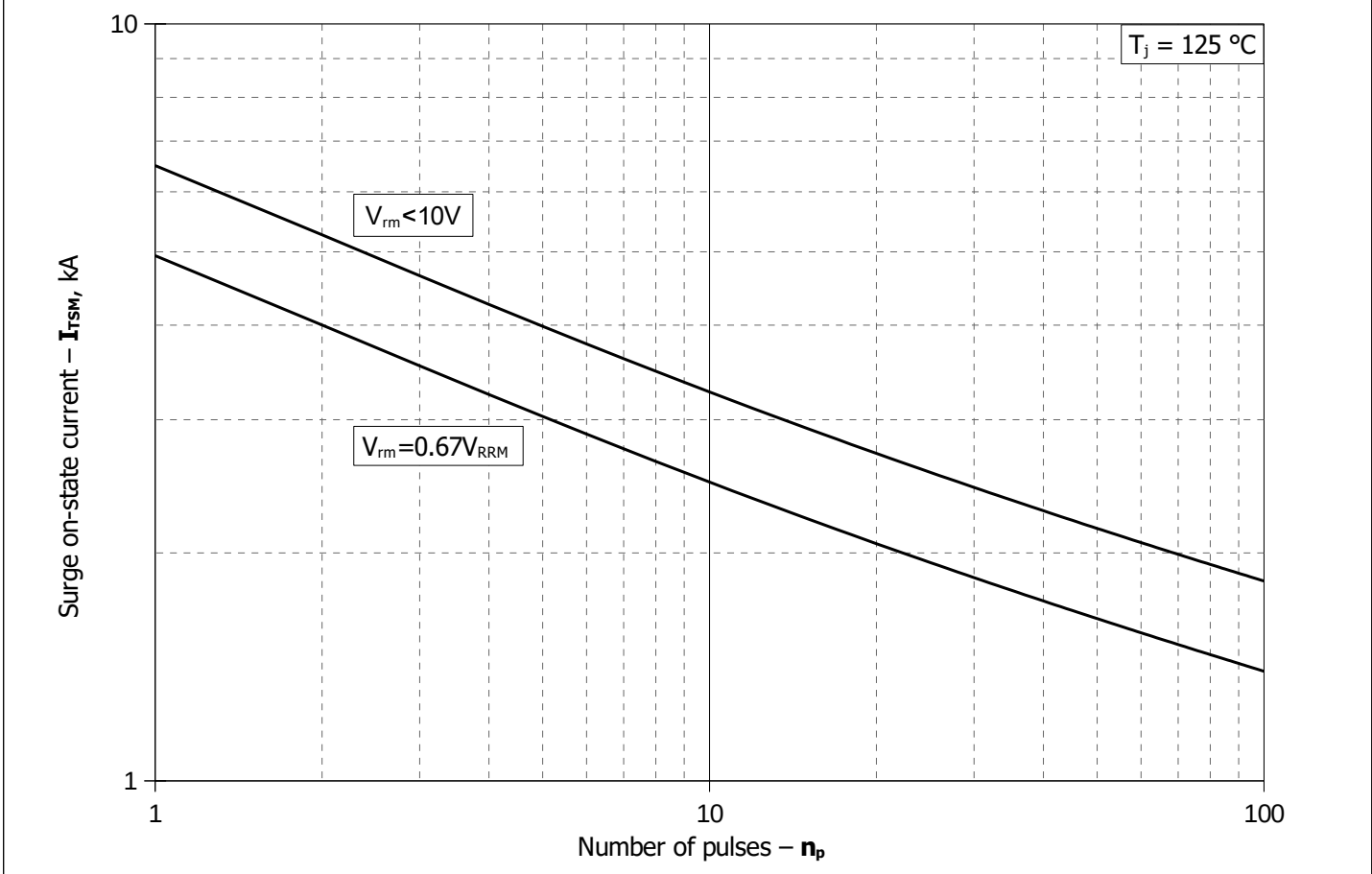


Fig. 14 - Maximum surge on-state current I_{TSM} vs. number of pulses n_p